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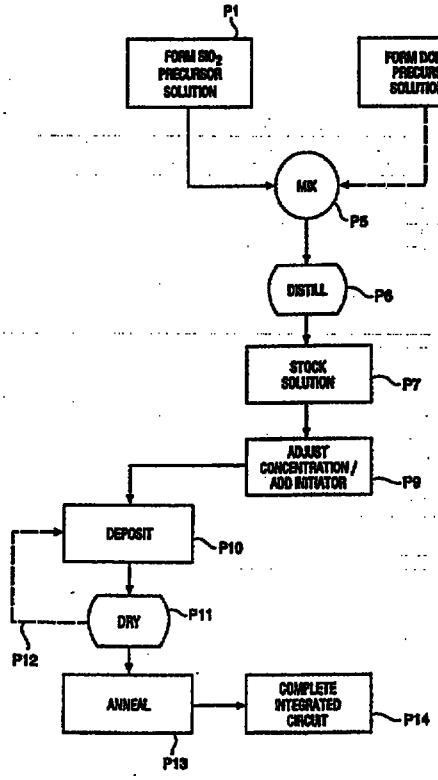
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(54) Title: METHOD AND APPARATUS FOR FABRICATING SILICON DIOXIDE AND SILICON GLASS LAYERS IN INTEGRATED CIRCUITS

(57) Abstract

A precursor liquid (64) comprising silicon in a xylene solvent is prepared, a substrate (5, 71) is placed within a vacuum deposition chamber (2), the precursor liquid is misted, and the mist (66) is flowed into the deposition chamber while maintaining the chamber at ambient temperature to deposit a layer of the precursor liquid on the substrate. The liquid is dried, baked, and annealed to form a thin film (1224, 77) of silicon dioxide or silicon glass on the substrate. Then an integrated circuit (100) is completed to include at least a portion of the silicon dioxide or silicon glass layer as an insulator (77) for an electronic device (76) in the integrated circuit.



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